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System Solution Guide - Preview

Uninterruptible Power Supply (UPS)



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Table of Contents

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Overview	
Applications	03
System Purpose	04
Market Information & Trends	
Global Market & Power Grid Anomalies	05
Modular UPS, Higher Power Density & Efficiency, Battery System	06
System Implementation	
Online, Offline and Line-interactive UPS	07
Solution Overview	
Block Diagram - Offline & Line-interactive UPS	08
Block Diagram - Online UPS	09
Topologies	10
AC-DC, DC-DC and DC-AC Stages	13
PFC Controllers	14
Silicon Carbide MOSFETs & Diodes	15
SiC JFETs & IGBT Discrete	16
Power Integrated Modules (PIM)	17
Gate Drivers	18



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Block Diagram - Online UPS

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Block Diagram - Online UPS

The block diagram below represents Online UPS solution created by onsemi. The online UPS provides continuous power by converting incoming AC to DC and then back to AC, ensuring a stable and uninterrupted power supply. onsemi offers a wide range of products, including discrete SiC and IGBT, power modules, isolated gate drivers, and power management controllers, to enhance systems with higher power density and efficiency.



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Discrete Solutions in UPS

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Silicon Carbide (SiC) JFET Portfolios

onsemi's new EliteSiC JFET product portfolios deliver best-in-class switching speed and ultra-low onresistance per unit area ($R_{DS(on)}$ x Area), translating into significantly higher system efficiency and reduced thermal losses in UPS systems. Furthermore, SiC JFETs are also an ideal choice for **static switches** by improving the performance and reliability.



SiC Combo JFETs

Key Features:

- 2 chips in 1 package \rightarrow Combo JFET
- Separate access to MOSFET and JFET gates
 → better switching dV/dt control
- Ultra low R_{DS(on)}, high pulse current
- 1200V, R_{DS(on)} ≤10mΩ
- 750V, $R_{DS(on)}$... $5m\Omega$ -10m Ω
- Target application: Solid state circuit breaker, disconnect switches

Learn more about SiC Combo JFET Portfolio





SiC Cascode JFETs

Key Features:

- 2 chips in co-packed Cascode
- Pick and place replacement for standard normally-off MOSFET
- Ultra low R_{DS(on)}, high pulse current
- 1700V, R_{DS(on)}... 410mΩ
- 1200V, R_{DS(on)}... 9mΩ 410mΩ
- 750V, R_{DS(on)} ... 5.4mΩ 58mΩ
- Target application: Power Supply, Inverters, On-board Chargers, DC-DC Converters

Learn more about <u>SiC Cascode JFET Portfolio</u>

IGBT Discrete

IGBTs are ideal for high voltage applications, since compared to the Si MOSFETs, they provides higher blocking voltage for the equivalent material thickness. IGBT switches are ideal to be used in DC/AC inverters and in the slow leg of the totem pole PFC.

Field Stop VII, IGBT, 1200V

- New Family of 1200 V Trench Field Stop VII IGBT
- Fast switching type suitable for high switching applications
- Improved parasitic cap for high-frequency operation
- Optimized diode for low V_F and softness



Figure 10: Comparison of switching losses of Field Stop VII in TO247-3 and TO247-4 packages



Figure 9: Switching-on losses of Field Stop VII $@V_{CE}=600V$

IGBT FGY4L140T120SWD

- 1200V, 140A IGBT from FS7 family
- TO247-4 package has lower E_{on}, which enables higher switching frequency and power

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Power Integrated Modules (PIM) in UPS Systems

onsemi has shown outstanding performance in the industrial power integrated module (PIM) design area, using SiC MOSFET and IGBT technologies to enable UPS design improvements, including a PFC, DC/DC and Inverter modules using 1200 V SiC devices. SiC power devices are getting adopted fast in the Energy–infrastructure segment to improve efficiency or increase power density. Lower switching losses enable higher efficiency with less cooling efforts or higher switching frequency with reduced size and value of passive components. These benefits can justify the higher costs of SiC power devices.

Employing a SiC MOSFET module has proven to provide benefits in terms of electrical and thermal performance as well as power density. **onsemi** released its 2nd generation of 1200V SiC modules, with M3S MOSFET technology which is focused on improving switching performance and reduction of R_{DS(on)} * Area.

Table 3: SiC PIM Modules for UPS

Half-Bridge (2-Pack)	Full-Bridge (4-Pack)	T-Type & Vienna	Boost Stage Modules
Modules	Modules	Modules	
Half-Bridge SiC	Full-Bridge SiC	Recommended	Recommended
<u>PIM List</u>	<u>PIM List</u>	SiC PIM List	SiC PIM List

Full SiC PIM NXH011F120M3F2PTHG

SiC 1200V Full-Bridge module contains also a thermistor with HPS DBC in an F2 package.

- M3S MOSFET technology provides typical $R_{\text{DS(ON)}}$ = 11.3 m Ω at V_{GS} = 18V , I_{D} = 100A
- Use <u>Elite Power Simulator</u> and <u>PLECS Model</u> <u>Generator</u> to simulate wide range of power topologies with SiC modules

Full SiC PIM NXH008T120M3F2PTHG

T-type neutral point clamped converter (TNPC) SiC module based on 1200V M3S technology

• M3S MOSFET technology provides typical $R_{\text{DS(ON)}}$ = 8.5 m Ω at V_{GS} = 18V , I_{D} = 100A

IGBT PIM NXH800H120L7QDSG

1200V, 800A rated IGBT Half-Bridge power module with PIM11 (QD3) Package

- New Field Stop Trench 7 IGBT technology and Gen. 7 diodes provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability
- NTC Thermistor, Low Inductive Layout

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Table 4: IGBT and Hybrid PIM Modules for UPS

IGBT Based PIM Modules	Hybrid PIM Modules (IGBT + SiC)
Available PIM Modules (Various Topologies)	Available PIM Modules (Various Topologies)



Figure 8: Various onsemi Module Packages

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